Unit in mm

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL PLANAR TYPE

2 S C 2 6 4 4

VHF~UHF BAND WIDEBAND AMPLIFIER APPLICATIONS

- High Gain
- Low IMD
- $f_T = 4 \text{ GHz (Typ.)}$

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	v_{CBO}	25	V
Collector-Emitter Voltage	v_{CEO}	12	V
Emitter-Base Voltage	$V_{ m EBO}$	3.0	V
Collector Current	$^{\mathrm{I}}\mathrm{C}$	120	mA
Emitter Current	$I_{\mathbf{B}}$	40	mA
Collector Power Dissipation	$P_{\mathbf{C}}$	0.5	W
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

5.1 MAX 0.45 0.55 MAX 12.7 MIN 0.45

> BASE 2. EMITTER 3. COLLECTOR

JEDEC	TO-92	
EIAJ	SC-43	
TOSHIBA	2-5F1E	

Weight: 0.21 g

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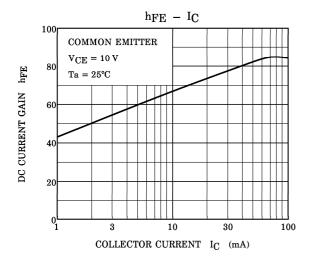
MICROWAVE CHARACTERISTICS (Ta = 25°C)

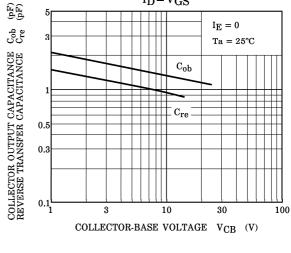
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Transition Frequency	$ m f_{T}$	$V_{CE} = 10 \text{ V}, I_{C} = 30 \text{ mA}$		4.0	_	GHz
Insertion Gain	$ S_{2le} ^2$ (1)	$V_{ m CE} = 10 m V, I_{ m C} = 30 m mA, \ f = 0.5 m GHz$		14.0	_	dB
	$ S_{2le} ^2$ (2)	$V_{ m CE} = 10 m V, IC = 30 mA, \ f = 1 m GHz$	_	8.5	_	dB
Noise Figure	NF (1)	$V_{ m CE} = 10 m V, I_{ m C} = 10 m mA, \ f = 0.5 m GHz$	_	2.3	_	dB
	NF (2)	$V_{ m CE} = 10 m V, I_{ m C} = 10 m mA, \ f = 1 GHz$	_	3.0	_	dB

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

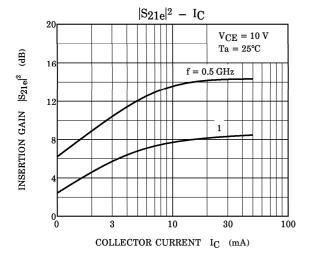
CHARACTERISTIC	SYMBOL	TEST CONDTION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 10 \text{ V}, I_{E} = 0$	_	_	1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 1.0 \text{ V}, I_{C} = 0$	_	_	10	μ A
DC Current Gain	${ m h_{FE}}$	$V_{CE} = 5 \text{ V}, I_{C} = 50 \text{ mA}$	20	50	_	_
Collector Output Capacitance	$C_{ m ob}$	$V_{CB} = 10 \text{ V}, I_{E} = 0,$		1.6	_	pF
Reverse Transfer Capacitance	$\mathrm{C_{re}}$	f = 1 MHz (Note)		1.1	_	pF

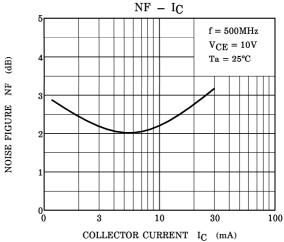
(Note) : C_{re} is measured by 3 terminal method with Capacitance Bridge.





 $I_D - V_{GS}$





COMMON EMITTER SMALL S-PARAMETERS OF 2SC2644

 $V_{CE} = 10 \text{ V}, I_{C} = 30 \text{ mA}$

